

ABSTRACT

SUPPORT FOR VERTICALLY-ORIENTED CAPACITORS DURING THE FORMATION OF A SEMICONDUCTOR DEVICE

A method for forming double-sided capacitors for a semiconductor device includes forming a dielectric structure which supports capacitor bottom plates during wafer processing. The structure is particularly useful for supporting the bottom plates during removal of a base dielectric layer to expose the outside of the bottom plates to form a double-sided capacitor. The support structure further supports the bottom plates during formation of a cell dielectric layer, a capacitor top plate, and final supporting dielectric. An inventive structure is also described.